



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: **Masayuki HATA**

Serial No.: **09/745,998**

Filed: **December 26, 2000**

Group Art Unit: **2814**

Examiner: **Douglas A. Wille**

P.T.O. Confirmation No.: **1371**

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TECHNOLOGY CENTER  
9/26/02

For. **LIGHT EMITTING DEVICE**

**AMENDMENT UNDER 37 CFR §1.111**

Commissioner for Patents  
Washington, D.C. 20231

September 18, 2002

Sir:

In response to the Office Action dated **April 19, 2002**, extended to **September 19, 2002**, by a two-month Petition for Extension of Time, please amend the above-identified application as follows:

**CLEAN VERSION OF AMENDMENTS**

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Please replace the paragraph beginning on page 34, line 9, with the following rewritten paragraph:

81  
As shown in Fig. 7, an n-type layer of the opposite conduction type 9 composed of GaN having a wider bandgap than that of the MQW light emitting layer 8 and having donor levels formed therein is formed on the side of a [0001] direction, that is, on the higher-energy side of the energy band of the MQW light emitting layer 8. The bandgap of the n-type layer of the opposite conduction type 9 is narrower than the bandgap of the p-type cladding layer 10 composed of p-AlGaIn, so that the refraction index of the n-type layer of the opposite conduction type 9 is higher than the refractive